

a Division of Serial No. 08/142,048, filed October 28, 1993, (now U.S. Patent 5,541,138)."

and insert the following copendency statement:

B1 This application is a Division of Serial No. 08/847,314 filed April 23, 1997 (now U.S. Patent 5,965,915); which itself is a Division of Serial No. 08/692,227, filed August 7, 1996 (now U.S. Patent 5,789,292); which is a Division of Serial No. 08/355,652, filed December 14, 1994 (now U.S. Patent 5,569,615); which is a Division of Serial No. 08/142,048, filed October 28, 1993, (now U.S. Patent 5,541,138).†

IN THE CLAIMS:

Kindly amend claims 12-14 and 16 as follows:

B2 12. (Amended) A transistor comprising according to claim 11, wherein each of the second impurity regions has a depth not deeper 50 [μm] nm.

13. (Amended) A transistor comprising:
a source region and a drain region, each of the source region and the drain region comprising an impurity at a first concentration;
a pair of [LDD] lightly doped drain (LDD) regions, each being adjacent to the source region and the drain region and comprising the impurity at a second concentration which is lower than the first concentration;
a channel region formed between the pair of LDD regions;
a gate electrode at least adjacent to the channel region having a gate insulating film therebetween,
wherein said channel region has a length not longer than 0.3 μm .

14. (Amended) A transistor comprising according to claim 13, wherein each of the LDD regions has a depth not deeper 50 [μm] nm.

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